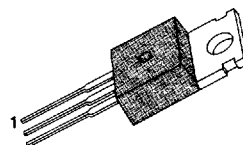


## FEATURES

- Lower  $R_{DS(on)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability

TO-220



1. Gate 2. Drain 3. Source

## PRODUCT SUMMARY

Part Number	V <sub>DS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
SSP6N60	600V	1.8Ω	6A
SSP6N55	550V	1.8Ω	6A

## ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	SSP6N60	SSP6N55	Unit
Drain-Source Voltage (1)	V <sub>DS</sub>	600	550	V <sub>DC</sub>
Drain-Gate Voltage (R <sub>GS</sub> =1.0MΩ)(1)	V <sub>DGR</sub>	600	550	V <sub>DC</sub>
Gate-Source Voltage	V <sub>GS</sub>	±20		V <sub>DC</sub>
Continuous Drain Current T <sub>C</sub> =25 °C	I <sub>D</sub>	6.0		A <sub>DC</sub>
Continuous Drain Current T <sub>C</sub> =100 °C	I <sub>D</sub>	4.0		A <sub>DC</sub>
Drain Current - Pulsed (3)	I <sub>DM</sub>	24		A <sub>DC</sub>
Gate Current - Pulsed	I <sub>GM</sub>	±1.5		A <sub>DC</sub>
Single Pulsed Avalanche Energy (4)	E <sub>AS</sub>	570		mJ
Avalanche Current	I <sub>AS</sub>	6.0		A
Total Power Dissipation at T <sub>C</sub> =25 °C	P <sub>D</sub>	125		Watts
Derate above 25 °C		1.0		W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150		°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T <sub>L</sub>	300		°C

Notes : (1) T<sub>J</sub>=25°C to 150°C

(2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

(4) L=27mH, V<sub>AS</sub>=50V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C

**ELECTRICAL CHARACTERISTICS** ( $T_C=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage					
	SSP6N60	600	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250 $\mu$ A
	SSP6N55	550	-	-	V	
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	-	4.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 $\mu$ A
I <sub>GSS</sub>	Gate-Source Leakage Forward	-	-	100	nA	V <sub>GS</sub> =20V
I <sub>GSS</sub>	Gate-Source Leakage Reverse	-	-	-100	nA	V <sub>GS</sub> =-20V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	-	-	250	$\mu$ A	V <sub>DS</sub> =Max. Rating, V <sub>GS</sub> =0V
		-	-	1000	$\mu$ A	V <sub>DS</sub> =0.8 Max. Rating, V <sub>GS</sub> =0V, T <sub>C</sub> =125 $^{\circ}$ C
I <sub>D(on)</sub>	On-State Drain-Source Current(2)	6.0	-	-	A	V <sub>DS</sub> $\geq$ 10V, I <sub>D</sub> =10V
R <sub>DS(on)</sub>	Static Drain-Source On Resistance(4)	-	-	1.8	$\Omega$	V <sub>GS</sub> =10V, I <sub>D</sub> =3.0A
				1.2	$\Omega$	V <sub>GS</sub> =10V, I <sub>D</sub> =3.0A
g <sub>fs</sub>	Forward Transconductance (2)	3.0	4.8	-	$\Omega$	V <sub>DS</sub> $\geq$ 50V, I <sub>D</sub> =3.0A
C <sub>iss</sub>	Input Capacitance	-	1800	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz
C <sub>oss</sub>	Output Capacitance	-	350	-	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	-	150	-	pF	
t <sub>d(on)</sub>	Turn-On Delay Time	-	30	-	ns	V <sub>DD</sub> =0.5 BV <sub>DSS</sub> , I <sub>D</sub> =6.0A, Z <sub>o</sub> =9.1 $\Omega$ (MOSFET switching times are essentially independent of operating temperature)
t <sub>r</sub>	Rise Time	-	75	-	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time	-	100	-	ns	
t <sub>f</sub>	Fall Time	-	60	-	ns	
Q <sub>g</sub>	Total Gate Charge (Gate-Source Plus Gate-Drain)	-	-	77	nC	V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A, V <sub>DS</sub> =0.8 Max. Rating (Gate charge is essentially independent of operating temperature)
Q <sub>gs</sub>	Gate-Source Charge	-	9.3	-	nC	
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	-	29.3	-	nC	

**THERMAL RESISTANCE**

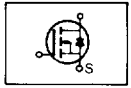
Symbol	Characteristics		All	Units	Remark
R <sub>thJC</sub>	Junction-to-Case	MAX	1.0	K/W	
R <sub>thCS</sub>	Case-to-Sink	TYP	0.5	K/W	Mounting surface flat smooth, and greased
R <sub>thJA</sub>	Junction-to-Ambient	MAX	62.5	K/W	Free Air Operation

Notes : (1) T<sub>J</sub>=25 $^{\circ}$ C to 150 $^{\circ}$ C(2) Pulse test : Pulse width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

(4) For Ultra low "A" R<sub>DS(on)</sub>, device add "A" suffix to part number

## SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
$I_S$	Continuous Source Current (Body Diode)	-	-	6.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier 
$I_{SM}$	Pulse Source Current (Body Diode) (3)	-	-	24.0	A	
$V_{SD}$	Diode Forward Voltage (2)	-	-	1.5	V	$T_J = 25^\circ\text{C}$ , $I_S = 10.0\text{A}$ , $V_{GS} = 0\text{V}$
$t_{rr}$	Reverse Recovery Time	-	450	940	ns	$T_J = 25^\circ\text{C}$ , $I_F = 10.0\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{S}$

Notes : (1)  $T_J = 25^\circ\text{C}$  to  $150^\circ\text{C}$ (2) Pulse test : Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ 

(3) Repetitive rating : Pulse width limited by max. junction temperature

